

GaAs PHEMT MMIC MEDIUM POWER AMPLIFIER, 7 - 15.5 GHz

Typical Applications

The HMC441LH5 is a medium PA for:

- Telecom Infrastructure
- Military Radio, Radar & ECM
- Space Systems
- Test Instrumentation

Features

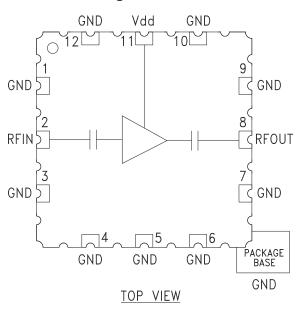
Gain: 5 dB

Saturated Power: +21.5 dBm @ 25% PAE

Single Positive Supply: +5V 50 Ohms Matched Input/Output Hermetic SMT Package, 25mm²

Screening to MIL-PRF-38535 (Class B or S) Available

Functional Diagram



General Description

The HMC441LH5 is a broadband 7 to 15.5 GHz GaAs PHEMT MMIC Medium Power Amplifier housed in a hermetic SMT leadless package. The amplifier provides 15 dB of gain and 21.5 dBm of saturated power at 25% PAE from a +5V supply. This 50 Ohm matched amplifier does not require any external components, and the RF I/Os are DC blocked, making it an ideal linear gain block or driver amplifier. The HMC441LH5 allows the use of surface mount manufacturing techniques and is suitable for high reliability military, industrial & space applications.

Electrical Specifications, $T_{\Delta} = +25^{\circ}$ C, Vdd = 5V

Parameter	Min.	Тур.	Max.	Min.	Тур.	Max.	Min.	Тур.	Max.	Min.	Тур.	Max.	Units
Frequency Range	7.0 - 8.0		8.0 - 13.0		13.0 - 14.0		14.0 - 15.5			GHz			
Gain	11	14		13	16		12	15		10.5	13.5		dB
Gain Variation Over Temperature		0.015	0.02		0.015	0.02		0.015	0.02		0.015	0.02	dB/ °C
Input Return Loss		11			13			10			8		dB
Output Return Loss		10			15			14			12		dB
Output Power for 1 dB Compression (P1dB)	15.5	18.5		17	20		16	19		16	19		dBm
Saturated Output Power (Psat)		20			21			21.5			21		dBm
Output Third Order Intercept (IP3)		30			32			32			32		dBm
Noise Figure		5.0			4.75			4.75			5.0		dB
Supply Current (Idd)		90	115		90	115		90	115		90	115	mA

HMC441LH5* PRODUCT PAGE QUICK LINKS

Last Content Update: 02/23/2017

COMPARABLE PARTS 🖵

View a parametric search of comparable parts.

EVALUATION KITS

• HMC441LH5 Evaluation Board

DOCUMENTATION

Application Notes

- AN-1363: Meeting Biasing Requirements of Externally Biased RF/Microwave Amplifiers with Active Bias Controllers
- Broadband Biasing of Amplifiers General Application Note
- MMIC Amplifier Biasing Procedure Application Note
- Thermal Management for Surface Mount Components General Application Note

Data Sheet

HMC441LH5 Data Sheet

TOOLS AND SIMULATIONS 🖵

HMC441LH5 S-Parameters

REFERENCE MATERIALS 🖵

Quality Documentation

Semiconductor Qualification Test Report: PHEMT-F (QTR: 2013-00269)

DESIGN RESOURCES \Box

- HMC441LH5 Material Declaration
- PCN-PDN Information
- · Quality And Reliability
- · Symbols and Footprints

DISCUSSIONS

View all HMC441LH5 EngineerZone Discussions.

SAMPLE AND BUY 🖳

Visit the product page to see pricing options.

TECHNICAL SUPPORT

Submit a technical question or find your regional support number.

DOCUMENT FEEDBACK 🖳

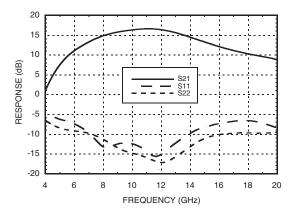
Submit feedback for this data sheet.



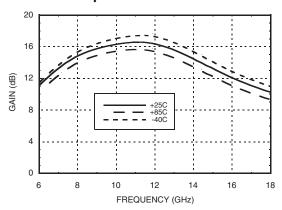


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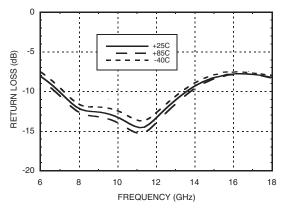
Broadband Gain & Return Loss



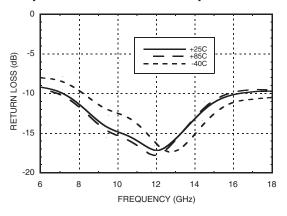
Gain vs. Temperature



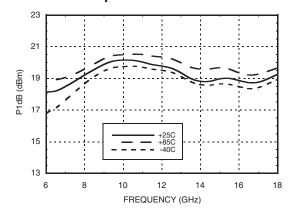
Input Return Loss vs. Temperature



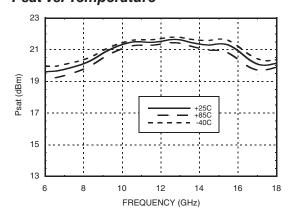
Output Return Loss vs. Temperature



P1dB vs. Temperature



Psat vs. Temperature

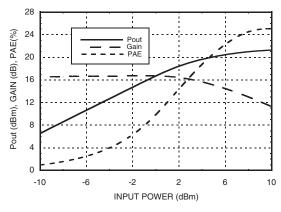




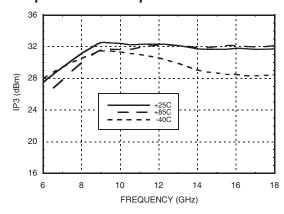


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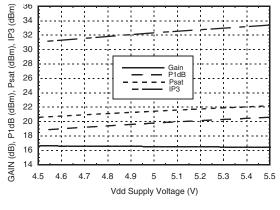
Power Compression @ 12 GHz



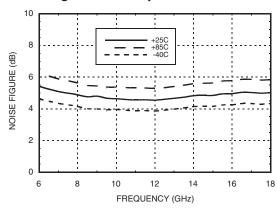
Output IP3 vs. Temperature



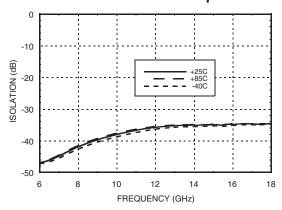
Gain, Power & Output IP3 vs. Supply Voltage @ 12 GHz



Noise Figure vs. Temperature



Reverse Isolation vs. Temperature







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Absolute Maximum Ratings

Drain Bias Voltage (Vdd)	+6 Vdc		
RF Input Power (RFIN)(Vdd = +5Vdc)	+15 dBm		
Channel Temperature	175 °C		
Continuous Pdiss (T = 85 °C) (derate 8.4 mW/°C above 85 °C)	0.76 W		
Thermal Resistance (channel to ground paddle)	118.8 °C/W		
Storage Temperature	-65 to +150 °C		
Operating Temperature	-40 to +85 °C		

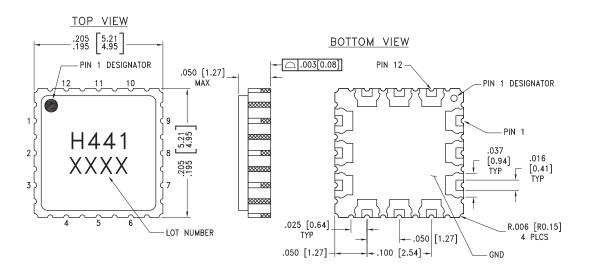
Typical Supply Current vs. Vdd

Vdd (V)	Idd (mA)
+5.5	92
+5.0	90
+4.5	88

Note: Amplifier will operate over full voltage range shown above



Outline Drawing



NOTES:

- PACKAGE BODY MATERIAL: CERAMIC & KOVAR
- 2. LEAD AND GROUND PADDLE PLATING: GOLD 40 80 MICROINCHES.
- 3 DIMENSIONS ARE IN INCHES IMILLIMETERS
- 4. LEAD SPACING TOLERANCE IS NON-CUMULATIVE
- 5. PAD BURR LENGTH 0.15mm MAX. PAD BURR HEIGHT 0.25mm MAX.
- 6. ALL GROUND LEADS AND GROUND PADDLE MUST BE SOLDERED TO PCB RF GROUND.





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Pin Descriptions

Pin Number	Function	Description	Interface Schematic		
1, 3-7, 9, 10, 12	GND	These pins and package bottom must be connected to RF/DC ground.	Ģ GND =		
2	RFIN	This pin is AC coupled and matched to 50 Ohms.	RFIN ○──		
8	RFOUT	This pin is AC coupled and matched to 50 Ohms.	— —○ RFOUT		
11	Vdd	Power Supply Voltage for the amplifier. External bypass capacitors are recommended.	Vdd ———————————————————————————————————		

Application Circuit

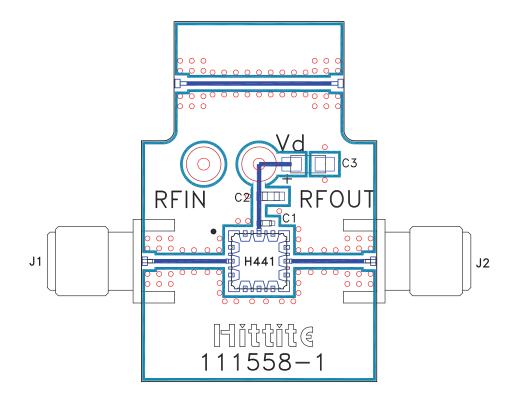
Component	Value	Vdd
C1	100 pF) O
C2	1,000 pF	
C3	4.7 µF	$\begin{array}{c ccccccccccccccccccccccccccccccccccc$
	RFIN	2 HMC441LH5 8 RFOUT





GaAs PHEMT MMIC MEDIUM POWER AMPLIFIER, 7 - 15.5 GHz

Evaluation PCB



List of Materials for Evaluation PCB 111560 [1]

Item	Description		
J1 - J2	PCB Mount SMA RF Connector, SRI		
U1	HMC441LH5		
C1	100 pF Capacitor, 0402 Pkg.		
C2	1,000 pF Capacitor, 0603 Pkg.		
C3	4.7 μF Capacitor, Tantalum		
PCB [2]	111558 Evaluation Board		

[1] Reference this number when ordering complete evaluation PCB

[2] Circuit Board Material: Rogers 4350

The circuit board used in the final application should use RF circuit design techniques. Signal lines should have 50 ohm impedance while the package ground leads and exposed paddle should be connected directly to the ground plane similar to that shown. A sufficient number of via holes should be used to connect the top and bottom ground planes. The evaluation circuit board shown is available from Hittite upon request.